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REMARKS

This is intended as a full and complete response to the Final Office Action dated February 24, 2004, having a shortened statutory period for response set to expire on May 24, 2004. Claims 22-38 remain pending in the application and stand rejected. Applicants have amended the claims as shown herein to clarify implicit aspects of the invention. As such, these amendments are not in response to the cited prior art or directed to the patentability of the invention. Therefore, these proposed amendments are not intended to narrow the claims or otherwise limit the scope of equivalents thereof. Further, these amendments do not raise new Issues or require an additional search. Accordingly, entry of these amendments is respectfully requested as is reconsideration of the pending claims for reasons discussed below.

Claims 22-23, 25-30, 33-35 and 37-38 stand rejected under 35 U.S.C. § 102(a) as being anticipated by WO 99/47731 to Chen. Claims 22, 24, 29, 31-32, and 35-36 also stand rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6.423.636 to Dordi.

Applicants respectfully traverse these rejections. Chen and Dordi, neither alone nor in combination, teach or suggest immersing a substrate into a plating solution while applying a bias to the substrate at a charge density between about 20 mA*sec/cm2 and about 160 mA*sec/cm2, as recited in base claims 22, 29, and 35 as well as those dependent therefrom. Both Chen and Dordi teach preferred processing limitations during the actual plating of a substrate after the substrate has been fully contacted with a plating bath. Particularly, the sections of those references cited by the Examiner. namely page 18, II. 4-9 and page 18, II. 8-9 of Chen and col. 9, II. 32-37; col. 7, II. 22-55; col. 9, Il. 15-47; and col. 11, Il. 21-26 of Dordi, each describe processing the substrate after the substrate is in full contact with the bath, not while introducing or immersing the substrate to the plating baths. Accordingly, the references, neither alone nor in combination, teach, show, or suggest immersing a substrate into a plating solution while applying a bias to the substrate as recited in all the claims. Withdrawal of the rejections and allowance of the claims is respectfully requested.

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Claims 11-12 and 16-17 stand provisionally rejected under 35 U.S.C. § 101 as claiming the same invention as that of claims 59, 67, 93 and 97 of copending Application No. 09/614,407. Claim 13 stands provisionally rejected under 35 U.S.C. § 101 as claiming the same invention as that of claims 69-71 of copending Application No. 09/614,407. Claim 14 stands provisionally rejected under 35 U.S.C. § 101 as claiming the same invention as that of claims 72-73 and 76-77 of copending Application No. 09/614,407.

Claims 1-21 were previously cancelled by the Applicants without prejudice to or disclaimer of the subject matter contained therein. As such, these double patenting rejections are moot, and withdrawal of the same is respectfully requested.

The secondary references made of record are noted. However, it is believed that the secondary references are no more pertinent to the Applicant's disclosure than the primary references cited in the Final Office Action. Therefore, Applicant believes that a detailed discussion of the secondary references is not necessary for a full and complete response to this Final Office Action. Further, Applicants are separately submitting a Supplemental Information Disclosure Statement and PTO Form 1449 for consideration.

Having addressed all issues set out in the Final Office Action. Applicant respectfully submits that the claims are in condition for allowance and respectfully request that the claims be allowed.

Respectfully submitted,

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